

MBR1545CT MBRB1545CT **MBR1545CT-1**



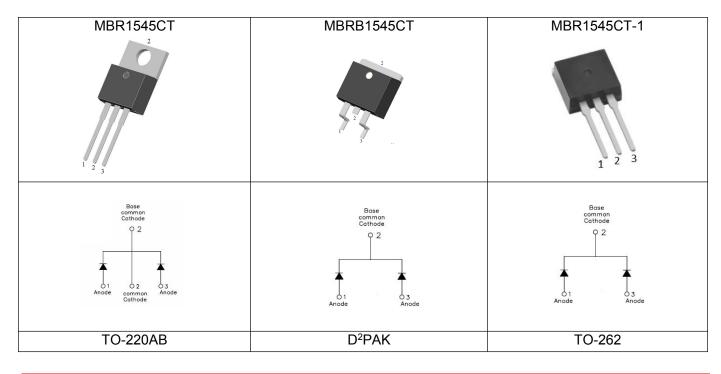
MBR1545CT/MBRB1545CT/MBR1545CT-1 SCHOTTKY RECTIFIER

Features

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- **Free-Wheeling diodes**
- **Reverse battery protection**



Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	45	V
Average Rectified Forward Current	IF (AV)	50% duty cycle @Tc=125°C, rectangular wave form	7.5(Per Leg) 15(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	180	A

• China - Germany - Korea - Singapore - United States • http://www.smc-diodes.com - sales@ smc-diodes.com -





RoHS 🗭

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.65	0.84	V
(Per Leg)*	V _{F2}	@ 15A, Pulse, TJ = 125 °C	0.60	0.72	V
Reverse Current (Per Leg)*	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.01	1.0	mA
	I _{R2}	$@V_R = rated V_R$ T _J = 125 °C	5	15	mA
Junction Capacitance(Per Leg)	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	360	400	pF
Typical Series Inductance (Per Leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 $\mu s, \ duty \ cycle < 2\%$

Thermal-Mechanical Specifications:

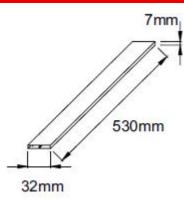
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case(Per Leg)	R _{θJC}	DC operation	3.0	°C/W
Typical Thermal Resistance, Junction to Case(Per package)	R _{θJA}	DC operation	60	°C/W
Typical Thermal Resistance, Case to Heat Sink	R _{0CS}	Mounting surface, smooth and greased	0.50	°C/W
Case Style		TO-220AB D ² PAK TO-	262	

Tube Specification

Device	Package	Weight	Shipping
MBR1545CT	TO-220AB	1.8g	50pcs / tube
MBRB1545CT	D ² PAK	1.85g	800pcs / reel
MBR1545CT-1	TO-262	1.85g	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification(TO-220AB/TO-262)





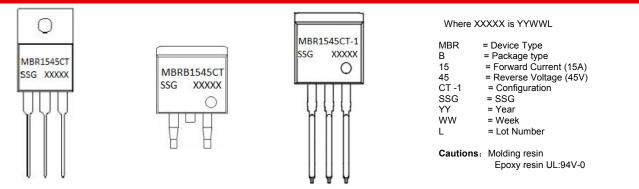
Ratings and Characteristics Curves

MBR1545CT MBRB1545CT MBR1545CT-1



Typical Forward Characteristics Typical Reverse Characteristics 10² 175℃ Instantaneous Reverse Current - I_R (mA) **150°**℃ 10¹ **125℃** 175°C 10⁰ **100°**℃ 10¹ **75℃** Instantaneous Forward Current - I $_{\rm F}$ (A) 10⁻¹ 50℃ 10⁻² 25°C 10⁻³ 125°C 0 10 20 50 30 40 Reverse Voltage - V_R (V) **Typical Junction Capacitance** 25℃ Junction Capacitance - C_T (pF) 400 350 25°(300 250 200 150 10⁰ 100 0.2 0.3 0.4 0.5 0.6 0.7 0.8 0 10 20 30 40 50 Forward Voltage Drop - V_F (V) Reverse Voltage - V_R (V)

Marking Diagram



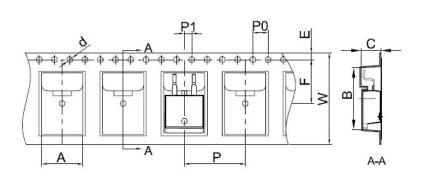
China - Germany - Korea - Singapore - United States http://www.smc-diodes.com - sales@ smc-diodes.com -



MBR1545CT MBRB1545CT MBR1545CT-1



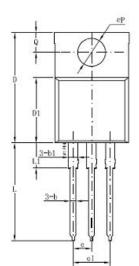
Carrier Tape Specification D2PAK

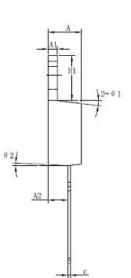


Symbol	Millimet	Villimeters	
Symbol	Min.	Max.	
А	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

Mechanical Dimensions TO-220AB







Symbol	Millimeters			
	Min.	Typical	Max.	
Α	4.42	4.57	4.72	
A1	1.17	1.27	1.37	
A2	2.52	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
D	14.94	15.24	15.54	
D1	8.85	9.00	9.15	
E	10.01	10.16	10.31	
e		2.54		
e1	4.98	5.06	5.18	
H1	6.04	6.24	6.44	
L	12.7	13.56	13.80	
L1	3.56	3.5	3.96	
ΦΡ	3.74	3.84	4.04	
Q	2.54	2.74	2.94	
Θ1		7 °		
Θ2		3°		
Θ3		4 °		



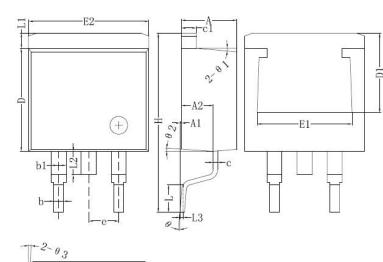
MBR1545CT MBRB1545CT MBR1545CT-1

RoHS

Pb

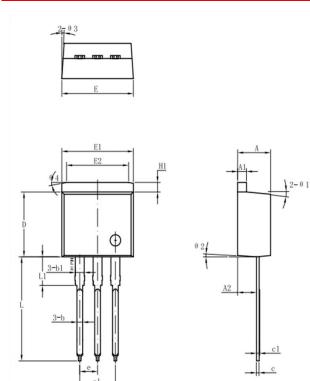
Technical Data Data Sheet N0736, Rev. A

Mechanical Dimensions D²PAK



Symbol	Millimeters				
5	Min.	Typical	Max.		
Α	4.47	4.70	4.85		
A1	0	0.10	0.25		
A2	2.59	2.69	2.89		
b	0.71	0.81	0.96		
b1	1.17	1.27	1.37		
С	0.31	0.38	0.61		
c1	1.17	1.27	1.37		
D	8.50	8.70	8.90		
D1	6.40				
E	10.01	10.16	10.31		
E1	7.6				
E2	9.98	10.08	10.31		
е		2.54			
н	14.6	15.1	15.6		
L	2.00	2.30	2.74		
L1	1.12	1.27	1.42		
L2	1.30		2.20		
L3		0.25BSC			
е	0	-	8°		
e1		5°			
e2		4 °			
e3		4 °			

Mechanical Dimensions TO-262



Symbol	Millimeters			
Symbol	Min.	Typical	Max.	
Α	4.55	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1		1.27		
С	0.36	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.55	8.70	8.85	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.18	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.70	
L1	1.17	1.27	1.40	
L2			2.20	
L3		0.25BSC		
e	0	-	8°	
e1		5°		
e2		4°		
e3		4°		

China - Germany - Korea - Singapore - United States
http://www.smc-diodes.com - sales@ smc-diodes.com







DISCLAIMER:

1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the SMC - Sangdest Microelectronics (Nanjing) Co., Ltd sales department for the latest version of the datasheet(s).

2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

3- In no event shall SMC - Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). SMC - Sangdest Microelectronics (Nanjing) Co., Ltd assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.

4- In no event shall SMC - Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.

5- No license is granted by the datasheet(s) under any patents or other rights of any third party or SMC - Sangdest Microelectronics (Nanjing) Co., Ltd.

6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of SMC -Sangdest Microelectronics (Nanjing) Co., Ltd.

7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.